

2N5152U3 & 2N5154U3

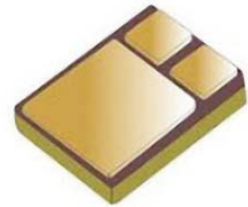


NPN Power Silicon Transistor

Rev. V3

Features

- Available in JAN, JANTX, JANTXV, JANS and JANSR per MIL-PRF-19500/544
- Lightweight & Low Power
- Ideal for Space, Military, and Other High Reliability Applications
- Surface Mount U3 Package



Electrical Characteristics (T_A = +25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	I _C = 100 mA dc; I _B = 0	V _{(BR)CEO}	V dc	80	—
Emitter - Base Cutoff Current	V _{EB} = 4.0 V dc; I _C = 0	I _{EBO1}	μA dc	—	1.0
	V _{EB} = 5.5 V dc; I _C = 0	I _{EBO2}	mA dc	—	1.0
Collector - Emitter Cutoff Current	V _{CE} = 60 V dc; V _{BE} = 0	I _{CES1}	μA dc	—	1.0
	V _{CE} = 100 V dc; V _{BE} = 0	I _{CES2}	mA dc	—	1.0
Collector - Emitter Cutoff Current	V _{CE} = 40 V dc; I _B = 0	I _{CEO}	μA dc	—	50
Forward Current Transfer Ratio	V _{CE} = 5.0 Vdc; I _C = 50 mA dc 2N5152U3	h _{FE}	-	20	—
	V _{CE} = 5.0 Vdc; I _C = 50 mA dc 2N5154U3			50	—
	V _{CE} = 5.0 Vdc; I _C = 2.5 A dc 2N5152U3			30	90
	V _{CE} = 5.0 Vdc; I _C = 2.5 A dc 2N5154U3			70	200
	V _{CE} = 5.0 Vdc; I _C = 5.0 A dc 2N5152U3			20	—
	V _{CE} = 5.0 Vdc; I _C = 5.0 A dc 2N5154U3			40	—
Collector - Emitter Saturation Voltage	I _C = 2.5 A dc; I _B = 250 mA dc	V _{CE(sat)1}	V dc	—	0.75
	I _C = 5.0 A dc; I _B = 500 mA dc	V _{CE(sat)2}	V dc	—	1.50
Base - Emitter Voltage (Non-Saturated)	V _{CE} = 5.0 V dc; I _C = 2.5 A dc	V _{BE}	V dc	—	1.45
Base - Emitter Saturation Voltage	I _C = 2.5 A dc; I _B = 250 mA dc	V _{BE(sat)1}	V dc	—	1.45
	I _C = 5.0 A dc; I _B = 500 mA dc	V _{BE(sat)2}	V dc	—	2.20
Magnitude of Common Emitter Small-Signal Short-Circuit, Forward Current, Transfer Ratio	V _{CE} = 5.0 Vdc; I _C = 500 mA dc; f = 10 MHz 2N5152U3 2N5154U3	h _{fe}	-	6 7	—
Common-Emitter, Small-Signal Short-Circuit Forward Current Transfer Ratio	V _{CE} = 5.0 V dc; I _C = 100 mA dc; f = 1 kHz 2N5152U3 2N5154U3	h _{fe}	-	20 50	—
Open-Circuit Output Capacitance	V _{CB} = 10 V dc, I _E = 0, f = 1 MHz	C _{obo}	pF	—	250

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Electrical Characteristics ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Cutoff Current	$T_C = +150^\circ\text{C}$ $V_{CE} = 60\text{ V dc}; V_{BE} = -2\text{ V dc}$	I_{CEX}	$\mu\text{A dc}$	—	25
Forward - Current Transfer Ratio	$T_C = -55^\circ\text{C}$ $V_{CE} = 5\text{ V dc}; I_C = 2.5\text{ A dc}$ 2N5152U3 2N5154U3	h_{FE4}	-	15 25	

Absolute Maximum Ratings ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Ratings	Symbol	Value
Collector - Emitter Voltage	V_{CEO}	80 V dc
Collector - Base Voltage	V_{CBO}	100 V dc
Emitter - Base Voltage	V_{EBO}	5.5 Vdc
Collector Current	I_C	2 A dc 10 A dc ⁽¹⁾
Reverse Pulse Energy ⁽²⁾		15 mj
Total Power Dissipation @ $T_C = +25^\circ\text{C}$ ⁽³⁾ @ $T_{SP} = +25^\circ\text{C}$	P_T	100 W 1 W
Operating & Storage Temperature Range	T_J, T_{STG}	-65°C to +200°C

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case ⁽⁴⁾	$R_{\theta JC}$	1.7°C/W
Thermal Resistance, Junction to Ambient ⁽⁴⁾	$R_{\theta JA}$	170°C/W ⁽⁵⁾

(1) This collector current value applies for $P_W \leq 8.3\text{ ms}$, duty cycle ≤ 1 percent.

(2) This rating is based on the capability of the transistors to operate safely in the unclamped inductive load energy test circuit, see subgroup 5 of the group A inspection table of MIL-PRF-19500/544.

(3) For derating, see figures 6, 7, 8 and 9 of MIL-PRF-19500/544.

(4) For thermal impedance curves, see figures 10, 11 and 12 of MIL-PRF-19500/544.

(5) Mounted on an FR4 printed circuit board.

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Electrical Characteristics ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Switching Characteristics					
Turn-On Time	$I_C = 5 \text{ A dc}; I_{B1} = 500 \text{ mA dc}, R_L = 6 \Omega,$ $I_{B2} = -500 \text{ mA dc}, V_{BE(\text{off})} = 3.7 \text{ Vdc}$	t_{on}	μs	—	0.5
Turn-Off Time		t_{off}	μs	—	1.5
Storage Time		t_s	μs	—	1.4
Fall Time		t_f	μs	—	0.5

Safe Operating Area

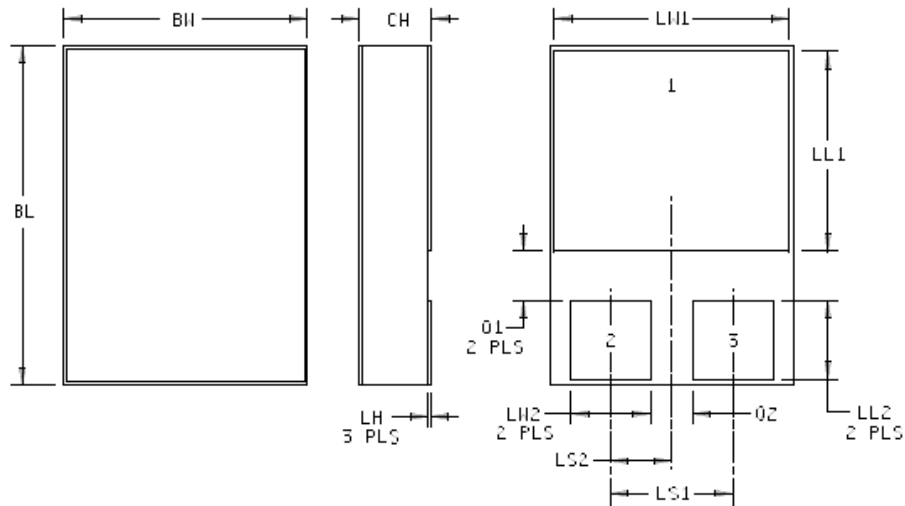
DC Tests:	$T_C = +25^\circ\text{C}, 1 \text{ Cycle}, t_p = 1 \text{ s}$
Test 1:	$V_{CE} = 5.0 \text{ V dc}; I_C = 2 \text{ A dc}$
Test 2:	$V_{CE} = 32 \text{ Vdc}; I_C = 310 \text{ mA dc}$
Test 3:	$V_{CE} = 80 \text{ Vdc}; I_C = 12.5 \text{ mA dc}$

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Outline Drawing (U3)



Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.395	.405	10.04	10.28
BW	.291	.301	7.40	7.64
CH	.1085	.1205	2.76	3.06
LH	.010	.020	0.25	0.51
LW1	.281	.291	7.14	7.41
LW2	.090	.100	2.29	2.54
LL1	.220	.230	5.59	5.84
LL2	.115	.125	2.93	3.17
LS1	.150 BSC		3.81 BSC	
LS2	.075 BSC		1.91 BSC	
Q1	.030		0.762	
Q2	.030		0.762	
TERM 1	Collector			
TERM 2	Base			
TERM 3	Emitter			

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.

FIGURE 2. Physical dimensions and configuration for surface mount (U3).

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